

Amendments to the Claims

Please cancel Claims 1-2, 5-18, 20-22, and amend Claims 3-4 as follows:

1-2. (Canceled)

3. (Currently Amended) The A method for fabricating a metal line of a semiconductor device, comprising the steps of:

- a) forming an insulation layer on a semiconductor substrate on which devices or lower lines are formed;
- b) forming a metal layer on the insulation layer;
- c) forming a photoresist pattern having an opening of less than or equal to 0.26  $\mu\text{m}$  width on the metal layer, wherein said photoresist has a thickness of less than 9000 Å;
- d) forming a buffer layer on the photoresist pattern, including in the opening ~~claim 2,~~ wherein the buffer layer comprises an oxide film of PE family; and
- e) selectively removing the metal layer at a lower side of the opening by dry etching to form a plurality of metal lines such that a dimension between adjacent metal lines is less than said certain width of said opening.

4. (Currently Amended) The A method for fabricating a metal line of a semiconductor device, comprising the steps of:

- a) forming an insulation layer on a semiconductor substrate on which devices or lower lines are formed;
- b) forming a metal layer on the insulation layer;
- c) forming a photoresist pattern having an opening of less than or equal to 0.26  $\mu\text{m}$  width on the metal layer, wherein said photoresist has a thickness of less than 9000 Å;

- d) forming a buffer layer on the photoresist pattern, including in the opening~~claim 3,~~  
wherein the buffer layer comprises an oxide film of PE family and has a thickness  
of 180 to 230Å; and
- e) selectively removing the metal layer at a lower side of the opening by dry etching  
to form a plurality of metal lines such that a dimension between adjacent metal  
lines is less than said certain width of said opening.

5-22. (Canceled)